

Title (en)
METHOD FOR CREATING A CARBON LAYER ON A STARTING STRUCTURE AND MICRO-ELECTROMECHANICAL OR SEMICONDUCTOR STRUCTURE

Title (de)
VERFAHREN ZUM ERZEUGEN EINER KOHLENSTOFFSCHICHT AUF EINER AUSGANGSSTRUKTUR UND MIKROELEKTROMECHANISCHE ODER HALBLEITER-STRUKTUR

Title (fr)
PROCÉDÉ POUR CRÉER UNE COUCHE DE CARBONE SUR UNE STRUCTURE DE DÉPART ET STRUCTURE MICROÉLECTROMÉCANIQUE OU SEMI-CONDUCTRICE

Publication
EP 3248211 A1 20171129 (DE)

Application
EP 15797674 A 20151120

Priority
• DE 102015201048 A 20150122
• EP 2015077240 W 20151120

Abstract (en)
[origin: WO2016116195A1] The invention relates to a method for creating a micro-electromechanical or semiconductor structure, comprising the following steps: providing an starting structure, the surface of which has at least sections consisting of silicon dioxide; providing a starting material, or a mixture of several starting materials, which release a mixture of carbon, silicon and chlorine in an LPCVD process; introducing the starting structure and the one, or the mixture of, starting material into the LPCVD process; and thereby separating a carbon layer on the sections of the starting structure consisting of silicon dioxide. The invention also relates to a micro-electromechanical or semiconductor structure which is produced according to the method.

IPC 8 full level
H01L 21/02 (2006.01); **H01L 29/66** (2006.01)

CPC (source: CN EP)
B81C 1/00373 (2013.01 - EP); **H01L 21/02447** (2013.01 - CN EP); **H01L 21/0245** (2013.01 - CN EP); **H01L 21/02488** (2013.01 - CN EP); **H01L 21/02527** (2013.01 - CN EP); **H01L 21/02529** (2013.01 - CN EP); **H01L 21/02576** (2013.01 - CN EP); **H01L 21/0262** (2013.01 - CN EP); **H01L 21/02639** (2013.01 - CN EP)

Citation (search report)
See references of WO 2016116195A1

Designated contracting state (EPC)
AL AT BE BG CH CY CZ DE DK EE ES FI FR GB GR HR HU IE IS IT LI LT LU LV MC MK MT NL NO PL PT RO RS SE SI SK SM TR

Designated extension state (EPC)
BA ME

DOCDB simple family (publication)
WO 2016116195 A1 20160728; CN 107112202 A 20170829; DE 102015201048 A1 20160728; EP 3248211 A1 20171129

DOCDB simple family (application)
EP 2015077240 W 20151120; CN 201580074163 A 20151120; DE 102015201048 A 20150122; EP 15797674 A 20151120